

Surface Mount Glass Passivated High Efficient Rectifier

SMAF(eSGB)			Features								
				DHS co ass pa gh forv eet MS maxir Ider di ompone d WEE . recog	ssivate vard su L leve num p p 260 ent in a EE 200	ed chij urge ca I 1, pe eak of °C / 4 accorc 02/96/\	apabil r J-ST 250 ° OS lance VC	D-020 C to RO	HS 20	02/95/	PB
Primary characteristics			Applications								
I _{F(AV)}		2A	Ideal	for ac-	-to-dc	bridge	full w	ave re	ctificat	tion su	ick as
V _{RRM}	50V t	o 1000V	SMPS, home applianes, office equipment, indusrial								
I _{FSM}	Ę	50A	automation applicatios								
I _{RM}	Ę	ōuA	4								
V _{FM} at I _F =2A		/1.7V	Mechanical data								
T _J max.		50 °C	• SMAF(eSGB)								
Maximum rating (Ta	a=25°C ι	unless othe	 Po Mo Re 	rminal: larity: ounting comm	As ma Torqu endec	rked. Je:10c	m-kg(8.8 inc			
Parameter						SMA	F(eS	SGB)			
			Sym	L2H1	L2H2		L2H4	, L2H5	L2H6	L2H7	Unit
Max. repetitive peak reverse	e voltage		Vrrm	50	100	200	400	600	800	1000	V
Max. RMS reverse voltage				35	70	140	280	420	560	700	V
Max. DC blocking voltage			V _{DC}	50	100	200	400	600	800	1000	V
Max. average forward current			IF(AV)	2						А	
Non-repetitive peak forward surge current											
Non-repetitive peak forward	l surge curi	ent	IFSM				50				А
8.3ms single half-sine-wave)		IFSM				50				A
8.3ms single half-sine-wave Max. instantaneous forward	e I voltage dr	op per diode	Ifsm Vfm		1.	3			1.7		A V
8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse	e I voltage dr e current	op per diode Ta=25 °C			1.	3	5		1.7		
8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltag	e I voltage dr e current e	op per diode	V _{FM}		1.		5 50	50	1.7		V µA
8.3ms single half-sine-wave Max. instantaneous forwarc Max. instantaneous reverse at rated DC blocking voltag Operating junction tempera	e I voltage dr e current e	op per diode Ta=25 °C	V _{FM} I _{RM} TJ		1.	-5	5 50 5 ~ +18		1.7		V
8.3ms single half-sine-wave Max. instantaneous forwarc Max. instantaneous reverse at rated DC blocking voltag	e I voltage dr e current e ture	op per diode Ta=25 °C Ta=125 °C	V _{FM}		1.	-5:	5 50		1.7		V μA °C

Notes:

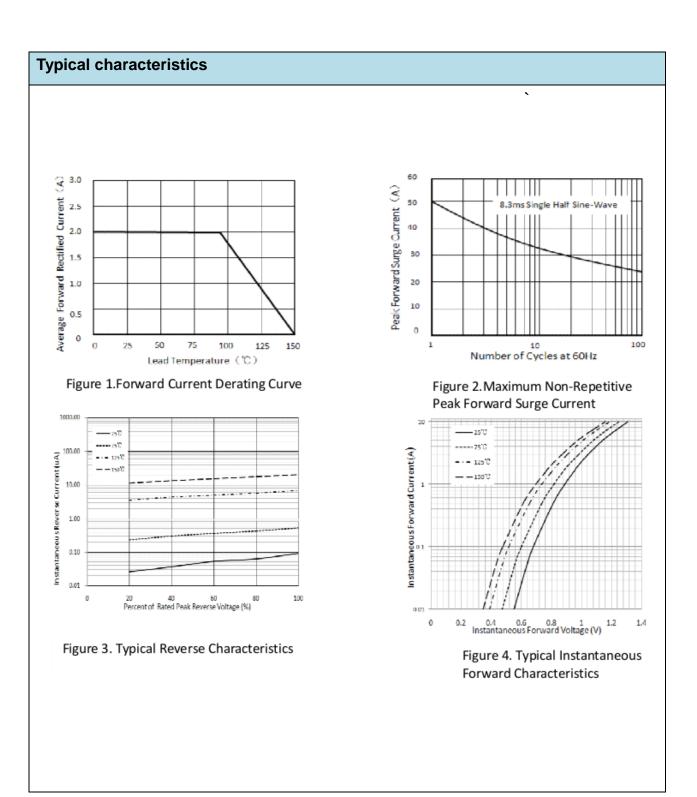
1 Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A

2. The thermal resistance from junction to mount, mounted on P.C.B with 8x8mm copper pads, 2 OZ, FR4 PCB

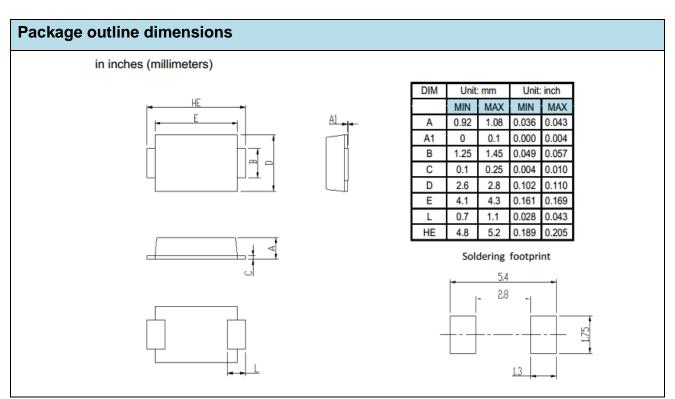


Surface Mount Glass Passivated High Efficient Rectifier

Ordering information (Example)									
PREFERRED	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE					
L2H7									







Golden SEMI Inc. - Legal Notice

Disclaimer - All data and specifications are subject to changes without notice

GOLDEN SEMI Inc, it's affiliates, agents, distributors and employees neither accept nor assume any responsibility for errors or inaccuracies. All data and specifications are intended for information and provide a product description only. Electrical and mechanical parameters listed in GOLDEN SEMI data sheets and specifications will vary dependent upon application and environmental conditions. GOLDEN SEMI is not liable for any damages occurred or resulting from any circuit, product or end-use application for which it's products are used. GOLDEN SEMI products are not intended or designed for use in life saving or sustaining apparatus and purchase of any GOLDEN SEMI products automatically indemnifies GOLDEN SEMI against any claims or damages resulting from application malfunction